

MOS FIELD EFFECT TRANSISTOR μ PA2521

N-CHANNEL MOS FET FOR SWITCHING

DESCRIPTION

The μ PA2521 is N-channel MOS Field Effect Transistor designed for DC/DC converter and power management applications of portable equipments.

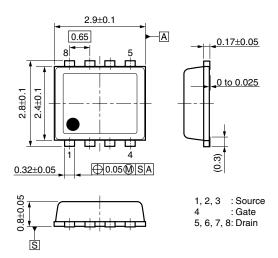
FEATURES

- Low on-state resistance
 - $R_{DS(on)1}$ = 16.5 m Ω MAX. (Vgs = 10 V, ID = 8.0 A)

 $R_{DS(on)2} = 25 \text{ m}\Omega \text{ MAX.} (V_{GS} = 4.5 \text{ V}, I_D = 4.0 \text{ A})$

- Built-in gate protection diode
- Small and surface mount package (8-pin VSOF (2429))
- Pb-free (This product does not contain Pb in external electrode and other parts.)

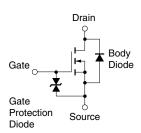
PACKAGE DRAWING (Unit: mm)



ABSOLUTE MAXIMUM RATINGS (TA = 25°C, All terminals are connected.)

Drain to Source Voltage (Vgs = 0 V)	VDSS	30	V
Gate to Source Voltage (VDS = 0 V)	Vgss	±20	V
Drain Current (DC)	I _{D(DC)}	±8	Α
Drain Current (pulse) Note1	ID(pulse)	±32	Α
Total Power Dissipation Note2	P _{T1}	1.0	W
Total Power Dissipation (PW = 5 sec) Note2	P _{T2}	2.2	W
Channel Temperature	Tch	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C
Single Avalanche Current Note3	las	8	Α
Single Avalanche Energy Note3	Eas	6.4	mJ

EQUIVALENT CIRCUIT



- **Notes 1.** PW \leq 10 μ s, Duty Cycle \leq 1%
 - 2. Mounted on FR-4 board of 25.4 mm x 25.4 mm x 0.8 mmt
 - 3. Starting T_{ch} = 25°C, V_{DD} = 15 V, R_G = 25 Ω , V_{GS} = 20 \rightarrow 0 V, L = 100 μ H

Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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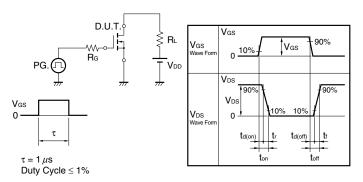
CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	IDSS	V _{DS} = 30 V, V _{GS} = 0 V			10	μΑ
Gate Leakage Current	Igss	V _{GS} = ±20 V, V _{DS} = 0 V			±10	μA
Gate to Source Cut-off Voltage	V _{GS(off)}	V _{DS} = 10 V, I _D = 1 mA	1.5		2.5	V
Forward Transfer Admittance Note	Yfs	V _{DS} = 10 V, I _D = 4.0 A	3.2			s
Drain to Source On-state Resistance Note	R _{DS(on)1}	V _{GS} = 10 V, I _D = 8.0 A		12	16.5	mΩ
	R _{DS(on)2}	V _{GS} = 4.5 V, I _D = 4.0 A		17	25	mΩ
Input Capacitance	Ciss	V _{DS} = 15 V,		780		pF
Output Capacitance	Coss	V _{GS} = 0 V,		170		pF
Reverse Transfer Capacitance	Crss	f = 1 MHz		61		pF
Turn-on Delay Time	t _{d(on)}	V _{DD} = 15 V, I _D = 4.0 A,		9.2		ns
Rise Time	tr	V _{GS} = 10 V,		3.8		ns
Turn-off Delay Time	t _{d(off)}	R _G = 10 Ω		31		ns
Fall Time	tf			4.8		ns
Total Gate Charge	Q _G	V _{DD} = 15 V,		7.6		nC
Gate to Source Charge	Qgs	V _{GS} = 5 V,		2.6		nC
Gate to Drain Charge	Q _{GD}	I _D = 8 A		2.4		nC
Body Diode Forward Voltage Note	V _{F(S-D)}	I _F = 8 A, V _{GS} = 0 V		0.82		V
Reverse Recovery Time	trr	I _F = 8 A, V _{GS} = 0 V,		24		ns
Reverse Recovery Charge	Qrr	di/dt = 100 A/ <i>μ</i> s		17		nC
Gate Resistance	R _G	f = 1 MHz		1.6		Ω

Note Pulsed

TEST CIRCUIT 1 AVALANCHE CAPABILITY

$V_{GS} = 20 \rightarrow 0 \text{ V}$ V_{DD} V_{DD} V_{DD} V_{DS} V_{DD} V_{DS} V_{DS} V_{DS} V_{DS} V_{DS} V_{DS}

TEST CIRCUIT 2 SWITCHING TIME



TEST CIRCUIT 3 GATE CHARGE

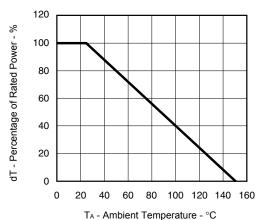
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 μ PA2521

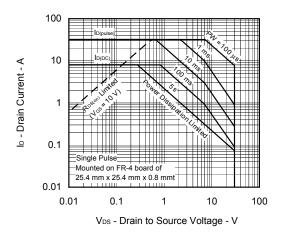
TYPICAL CHARACTERISTICS (TA = 25°C)

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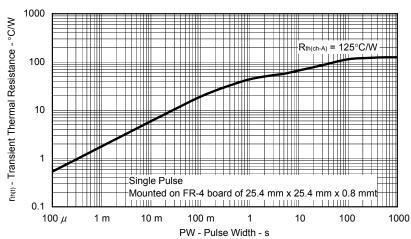
DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



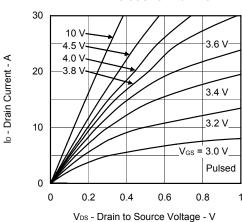
FORWARD BIAS SAFE OPERATING AREA



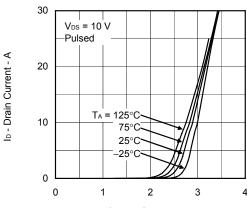
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



FORWARD TRANSFER CHARACTERISTICS

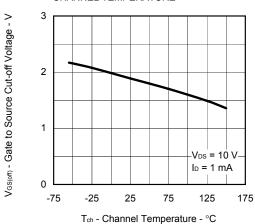


V_{GS} - Gate to Source Voltage - V

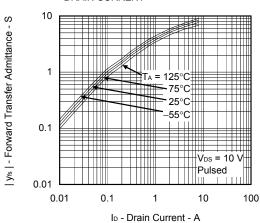
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 $\mathsf{R}_{\mathsf{DS}(\mathsf{on})}$ - Drain to Source On-state Resistance - m Ω

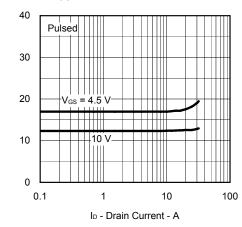
GATE TO SOURCE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE



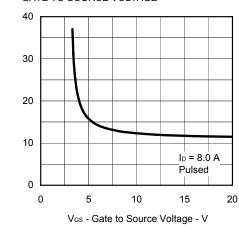
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



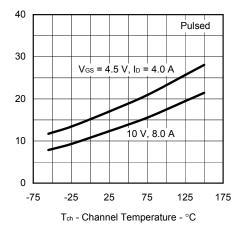
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



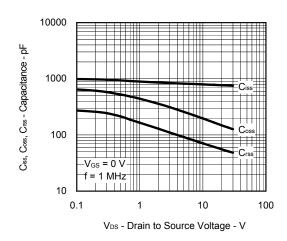
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE

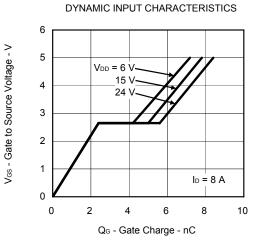


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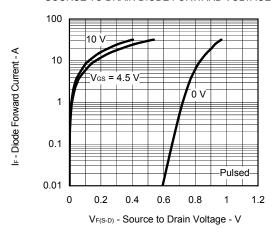
R_{DS(m)} - Drain to Source On-state Resistance - mΩ

R_{DS(m)} - Drain to Source On-state Resistance - mΩ

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SOURCE TO DRAIN DIODE FORWARD VOLTAGE



ORDERING INFORMATION

PART NUMBER	LEAD PLATING	PACKING	PACKAGE
μPA2521T1H-T1-AT Note		8 mm embossed taping	
μPA2521T1H-T2-AT Note	Pure Sn	3000 p/reel	8-pin VSOF (2429)

Note Pb-free (This product does not contain Pb in external electrode and other parts.)

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